



IRLU7843-701PBF Information



For Reference Only

Part Number IRLU7843-701PBF **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 161A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRLU7843-701PBF Specifications

Manufacturer Part Number IRLU7843-701PBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 161A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 50nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 4380pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 140W (Tc) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
CategoryDiscrete Semiconductor ProductsFackageTO-251-3 Short Leads, IPak, TO-251AASeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C161A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs50nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4380pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package1-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Manufacturer Part Number	IRLU7843-701PBF
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Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 161A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 50nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 4380pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 140W (Tc) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET Type Rochannel Technology MOSFET (Metal Oxide) MOSFET (Metal Oxide) 30V Current - Continuous Drain (Id) @ 25°C 161A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) 30V AUSFET (Metal Oxide) 30V 161A (Tc) 161A (Tc)	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C161A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs50nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4380pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	HEXFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C161A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs50nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds4380pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 161A (Tc) 162 161A (Tc) 162 161A (Tc) 161A (Tc) 162 161A (Tc) 161A (Tc) 161A (Tc) 162 161A (Tc) 161A (Tc) 162 161A (Tc) 162 161A (Tc) 161 161A (Tc) 161 161 161 161 161 161 161 1	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole Supplier Device Package Package / Case 2.3V @ 250μA	Current - Continuous Drain (Id) @ 25°C	161A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 4380pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	2.3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	50nC @ 4.5V
FET Feature - Power Dissipation (Max) 140W (Tc) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	4380pF @ 15V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	140W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	3.3 mOhm @ 15A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

IRLU7843-701PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLU7843-701PBF Payment Methods





















IRLU7843-701PBF Shipping Methods













If you have any question about IRLU7843-701PBF, please do not hesitate to contact us!

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